

L Number	Hits	Search Text	DB	Time stamp
22	13656	second near3 ((gate or scan\$4) and insulat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/10 11:19
23	16	((((insulat\$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo) or (silver or ag))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal\$4) near3 (line or electrode))) and (passivation near3 (film or layer or plate or coat\$4))) and ((dielectric or permittiv\$4) near3 (constant or coefficient))) and 349/\$6) and (second near3 ((gate or scan\$4) and insulat\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/10 11:20
24	7610	(second near3 insulat\$4) same (nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/10 11:20
25	8	((((insulat\$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo) or (silver or ag))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal\$4) near3 (line or electrode))) and (passivation near3 (film or layer or plate or coat\$4))) and ((dielectric or permittiv\$4) near3 (constant or coefficient))) and 349/\$6) and ((second near3 insulat\$4) same (nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/10 11:21
26	12	"a-si:c:o" or "a-si:o:f"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/10 11:26
27	3	("a-si:c:o" or "a-si:o:f") and 349/\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/10 11:26
-	34614	349/\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 08:42
-	1645	((thin near3 film near "3" transistor) or (tft)) and substrate and ((signal or gate or signaling) near3 (line or electrode)) and array and insulat\$4 and dielectric and (pixel near4 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 08:53
-	811	349/\$6 and (((thin near3 film near "3" transistor) or (tft)) and substrate and ((signal or gate or signaling) near3 (line or electrode)) and array and insulat\$4 and dielectric and (pixel near4 electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 08:45
-	113819	silicon near3 nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:22

-	1380	((thin near3 film near "3" transistor) or (tft)) and substrate and ((signal or data or signaling) near3 (line or electrode)) and array and insulat\$4 and dielectric and (pixel near4 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 08:46
-	1708	((thin near3 film near3 transistor) or (tft)) and substrate and ((signal or gate or signaling) near3 (line or electrode)) and array and insulat\$4 and dielectric and (pixel near4 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:20
-	1728	((thin near3 film near3 transistor) or (tft)) and substrate and ((signal or gate or signaling or scan\$4 or data) near3 (line or electrode)) and array and insulat\$4 and dielectric and (pixel near4 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:20
-	576	((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data) near3 (line or electrode)) and array and insulat\$4 and dielectric and (pixel near4 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:21
-	418	((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data) near3 (line or electrode)) and array and insulat\$4 and (dielectric near "6" constant) and (pixel near4 electrode) and hole	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:01
-	118878	silicon near3 nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:23
-	295	((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data) near3 (line or electrode)) and array and insulat\$4 and (dielectric near "6" constant) and (pixel near4 electrode) and hole) and (silicon near3 nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:23
-	241750	(indium near3 (tin or zinc) near3 oxide) or ito or izo	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:24
-	236208	(indium adj (tin or zinc) adj oxide) or ito or izo	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:24
-	277	((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data) near3 (line or electrode)) and array and insulat\$4 and (dielectric near "6" constant) and (pixel near4 electrode) and hole) and (silicon near3 nitride)) and ((indium adj (tin or zinc) adj oxide) or ito or izo)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:24
-	4402	((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:25

-	203	((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data) near3 (line or electrode)) and array and insulat\$4 and (dielectric near "6" constant) and (pixel near4 electrode) and hole) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:25
-	790203	chrom\$4 or cr	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:11
-	4230267	aluminum or al	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:12
-	150	((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data) near3 (line or electrode)) and array and insulat\$4 and (dielectric near "6" constant) and (pixel near4 electrode) and hole) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))) and (chrom\$4 or cr) and (aluminum or al)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:45
-	448074	molybdenum or mo	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:46
-	96476	(chrom\$4 or cr) and (aluminum or al) and (molybdenum or mo)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:47
-	243803	((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo)) near5 alloy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:49
-	87	((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data) near3 (line or electrode)) and array and insulat\$4 and (dielectric near "6" constant) and (pixel near4 electrode) and hole) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))) and ((chrom\$4 or cr) and (aluminum or al) and (molybdenum or mo)) and (((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo)) near5 alloy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:53
-	67	(((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data or drain or source) near3 (line or electrode)) and array and insulat\$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:13

-	54	(((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data or drain or source) near3 (line or electrode)) and array and insulat\$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon near3 nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:02
-	51	(((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data or drain or source) near3 (line or electrode)) and array and insulat\$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:02
-	34	(((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data or drain or source) near3 (line or electrode)) and array and insulat\$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:04
-	33	((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data or drain or source) near3 (line or electrode)) and array and insulat\$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))) and (((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:05
-	1426	349/43	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:10
-	2218	349/42	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:05
-	3078	349/43 or 349/42	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:06
-	11	((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data or drain or source) near3 (line or electrode)) and array and insulat\$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))) and (((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (349/43 or 349/42)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:10
-	358	349/51	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:10

-	89	349/52	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:10
-	3427	349/43 or 349/42 or 349/51 or 349/52	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:11
-	11	(((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data or drain or source) near3 (line or electrode)) and array and insulat\$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))) and ((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (349/43 or 349/42 or 349/51 or 349/52)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:11
-	6754	insulat\$4 near8 (dielectric and silicon near3 nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:12
-	90796	(gate or scan\$4) near8 ((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:14
-	42185	((thin near3 film near3 transistor) or (tft)) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:14
-	706656	(drain or data or source or signal\$4) near3 (line or electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:15
-	718	(insulat\$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal\$4) near3 (line or electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:15
-	32786	passivation near3 (film or layer or plate or coat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:16
-	290	((insulat\$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal\$4) near3 (line or electrode))) and (passivation near3 (film or layer or plate or coat\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:29

-	1799	(passivation near3 (film or layer or plate or coat\$4)) same ((chemical near3 vapor near3 deposit\$3) or pevcd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:31
-	21	((insulat\$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal\$4) near3 (line or electrode))) and ((passivation near3 (film or layer or plate or coat\$4)) same ((chemical near3 vapor near3 deposit\$3) or pevcd))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:17
-	152	349/\$6 and (((insulat\$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal\$4) near3 (line or electrode))) and (passivation near3 (film or layer or plate or coat\$4)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:18
-	6	349/\$6 and (((insulat\$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal\$4) near3 (line or electrode))) and ((passivation near3 (film or layer or plate or coat\$4)) same ((chemical near3 vapor near3 deposit\$3) or pevcd)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:18
-	138	((insulat\$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal\$4) near3 (line or electrode))) and (passivation near3 (film or layer or plate or coat\$4))) and ((dielectric or permittiv\$4) near3 (constant or coefficient))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:30
-	74	(((((insulat\$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal\$4) near3 (line or electrode))) and (passivation near3 (film or layer or plate or coat\$4))) and ((dielectric or permittiv\$4) near3 (constant or coefficient))) and 349/\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:30
-	32	(((((insulat\$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal\$4) near3 (line or electrode))) and (passivation near3 (film or layer or plate or coat\$4))) and ((dielectric or permittiv\$4) near3 (constant or coefficient))) and 349/\$6) and ((chemical near3 vapor near3 deposit\$3) or pevcd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/10 10:57